



DC COMPONENTS CO., LTD.
DISCRETE SEMICONDUCTORS

DCR100-3
THRU
DCR100-8

TECHNICAL SPECIFICATIONS OF SENSITIVE GATE SILICON CONTROLLED RECTIFIERS
VOLTAGE RANGE - 100 to 600 Volts
CURRENT - 0.8 Ampere

Description

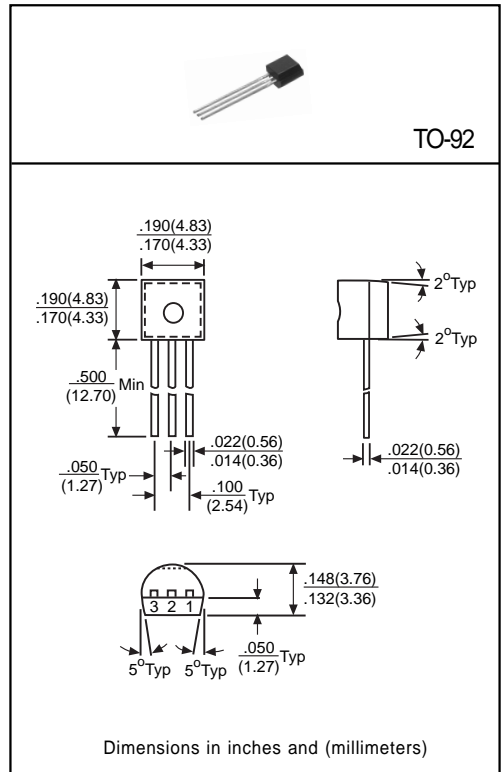
- * Driven directly with IC and MOS device
- * Feature proprietary, void-free glass passivated chips
- * Available in voltage ratings from 100 to 600 volts
- * Sensitive gate trigger current
- * Designed for high volume, line-powered control application in relay lamp drivers, small motor controls, gate drivers for large thyristors

Pinning

1 = Cathode, 2 = Gate, 3 = Anode

Absolute Maximum Ratings($T_A=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Peak Repetitive Off-State Voltage and Reverse Voltage	DCR100-3 DCR100-4 DCR100-6 DCR100-8 V_{DRM}, V_{RRM}	100 200 400 600	V
On-State RMS Current ($T_A=57^{\circ}C, 180^{\circ}$ Conduction Angles)	$I_{T(RMS)}$	0.8	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60Hz)	I_{TSM}	8	A
Forward Peak Gate Current(For 3 μ sec.)	I_{GM}	0.8	A
Forward Peak Gate Power Dissipation	P_{GM}	0.1	W
Forward Average Gate Power Dissipation	$P_{G(AV)}$	0.01	W
Reverse Peak Gate Voltage	V_{GRM}	6.0	V
Operating Junction Temperature	T_J	-40 to +110	$^{\circ}C$
Storage Temperature	T_{STG}	-40 to +150	$^{\circ}C$



Electrical Characteristics

(Ratings at 25 $^{\circ}C$ ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Peak Repetitive Forward or Reverse Off-State Blocking Current	I_{DRM}, I_{RRM}	-	-	10	μA	$V_{AK}=\text{Rated } V_{DRM} \text{ or } V_{RRM}$ $R_{\theta K}=1K\Omega$
				200		
Peak Forward On-State Voltage	V_{TM}	-	-	1.7	V	$I_{TM}=0.8A \text{ Peak}, T_C=25^{\circ}C$
Continuous DC Gate Trigger Current	I_{GT}	-	-	200	μA	$V_{AK}=7V \text{ DC}, R_L=100\Omega$
Continuous DC Gate Trigger Voltage	V_{GT}	-	-	0.8	V	$V_{AK}=7V \text{ DC}, R_L=100\Omega$
DC Holding Current	I_H	-	-	10	mA	$R_{\theta K}=1K\Omega, \text{ Gate Open}$
Critical Rate-of-Rise of Off-State Voltage	dv/dt	-	5	-	V/ μs	$R_{\theta K}=1K\Omega, \text{ Gate Open}$
Gate Controlled Turn-on Time(t_b+t_r)	T_{gt}	-	2.2	-	μsec	$I_{GT}=10mA$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	-	75	-	$^{\circ}C/W$	-